

Patent Attorney's Docket No. <u>015290-457</u>

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| In re P                     | Patent Application of   | )                                |             |
|-----------------------------|---|----------------------------------|-------------|
| Jerome S. HUBACEK et al.    |   | ) Group Art Unit: 1763           | #20A        |
| Application No.: 09/749,916 |   | ) Examiner: L. L. Alejandro Mule | ro 8/12/02  |
| Filed:                      | December 29, 2000   | ) Confirmation No.: 6834         | Mu          |
| For:                        | ELECTRODE FOR PLASMA PROCESSES AND METHOD FOR MANUFACTURE AND USE THEREOF | TC 1/00                          | RE(         |
| <u>AMENDMENT</u>            |   |                                  |             |
|                             | tant Commissioner for Patents ington, D.C. 20231                          | MOOW                             | AED SERVICE |
| Sir:                        |   | <u> </u>                         |             |

In response to the Official Action dated April 4, 2002, the period for response having been extended until August 4, 2002 by a Petition for a One Month Extension of Time submitted herewith, please amend the above-identified application as follows:

## **IN THE CLAIMS:**

Please cancel Claims 11-20 without prejudice or disclaimer of the subject matter thereof, replace Claim 1 and add new Claims 21-30 as follows:

1. (Amended) A low resistivity silicon electrode adapted to be mounted in a plasma reaction chamber used in serviconductor substrate processing, comprising:

a silicon electrode having a thickness of at least about 0.3 inch an electrical resistivity of less than 1 ohm-cm, the electrode having an RF driven or electrically grounded surface on one side thereof, the surface being exposed to plasma in the plasma reaction chamber during use of the electrode.